



The DNA of tech.®

1200 V SiC MOSFET Power Modules in SOT-227 Package

Offer Drop-in Replacements for Competing Solutions in Medium to High Frequency Applications



ADVANTAGE

Designed to reduce switching losses and increase power efficiency, feature latest generation silicon carbide (SiC) in industry-standard SOT-227 package

KEY PRODUCT FEATURES

- ✓ Offered in single switch and low side chopper configurations
- ✓ Electrical insulation up to 2500 V for one minute
- ✓ Continuous drain current from 50 A to 200 A
- ✓ Low on-resistance down to 12.1 mΩ
- ✓ High speed switching with low capacitance
- ✓ Maximum operating junction temperature of +175 °C



RESOURCES

MARKETS AND APPLICATIONS



CONNECTIVITY

- Telecom mobile infrastructure



MOBILITY

- Charging stations



ENERGY SECTOR

- Generation and exploration
- Storage



INDUSTRIAL

- Drives and tools
- Infrastructure

KEY SPECIFICATIONS TABLE

Part Number	V _{DSS} (V)	I _D (A)	R _{DS(ON)} (mΩ)	Configuration
VS-SF50LA120	1200	50	43	Low side chopper
VS-SF50SA120		50	47	Single switch
VS-SF100SA120		100	23	Single switch
VS-SF150SA120		150	16.8	Single switch
VS-SF200SA120		200	12.1	Single switch



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